WeEn
WeEn Semiconductors

BTA201-800ER

3Q Hi-Com Triac

Rev.03 - 19 October 2021 — Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO92 plastic package. This "series ER" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers. It has reverse pinning to that of the standard triac in this package.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Reverse pinning version (ER)
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

3. Applications

- General purpose motor control circuits
- Small loads in washing machines
- Solenoid drivers

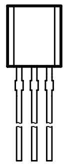
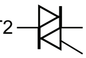
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Absolute maximum rating							
V_{DRM}	repetitive peak off-state voltage			-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 54$ °C; Fig. 1; Fig. 2; Fig. 3		-	-	1	A
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 0.1$ A; T2+ G+ $T_j = 25$ °C; Fig. 7		1	-	10	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2+ G- $T_j = 25$ °C; Fig. 7		1	-	10	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G- $T_j = 25$ °C; Fig. 7		1	-	10	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 TO-92 (SOT54)	
2	G	gate		
3	T2	main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA201-800ER	TO92	BTA201-800ER,412	Bulk	1000	SOT54	14-Nov-2013
BTA201-800ER	TO92	BTA201-800ER,126	Ammo	2000	SOT54 wide pitch	14-Nov-2013
BTA201-800ER	TO92	BTA201-800ER,112	Bulk	1000	SOT54	14-Nov-2013
BTA201-800ER	TO92	BTA201-800ER,116	Reel	2000	SOT54 wide pitch	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA201-800ER	201-8ER

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 54$ °C; Fig. 1; Fig. 2; Fig. 3		-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5		-	12.5	A
		full sine wave; t_p = 16.8 ms; $T_{j(init)}$ = 25 °C		-	13.7	A
I^2t	I^2t for fusing	t_p = 10 ms; SIN		-	0.78	A^2s
dI_T/dt	rate of rise of on-state current	I_G = 0.2 A		-	100	A/µs
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.1	W
T_j	junction temperature			-40	125	°C

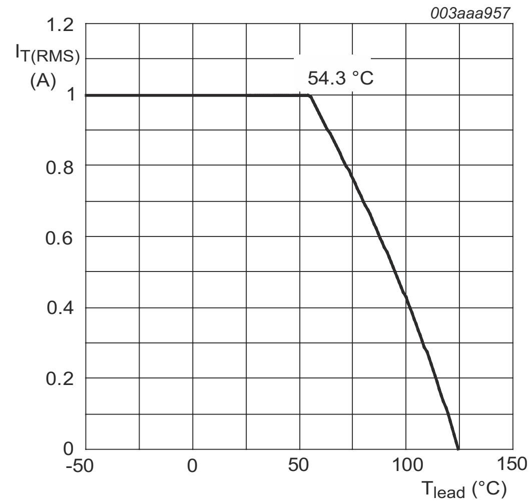
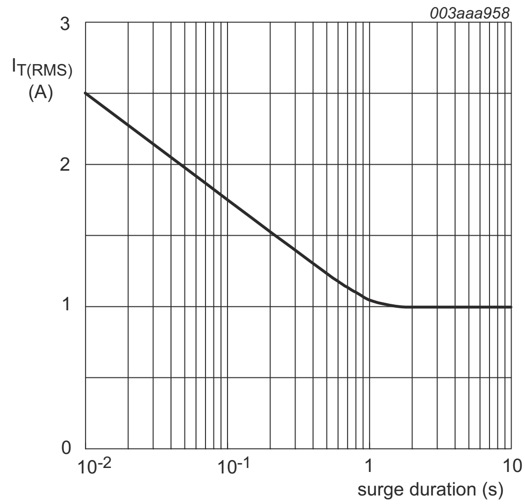
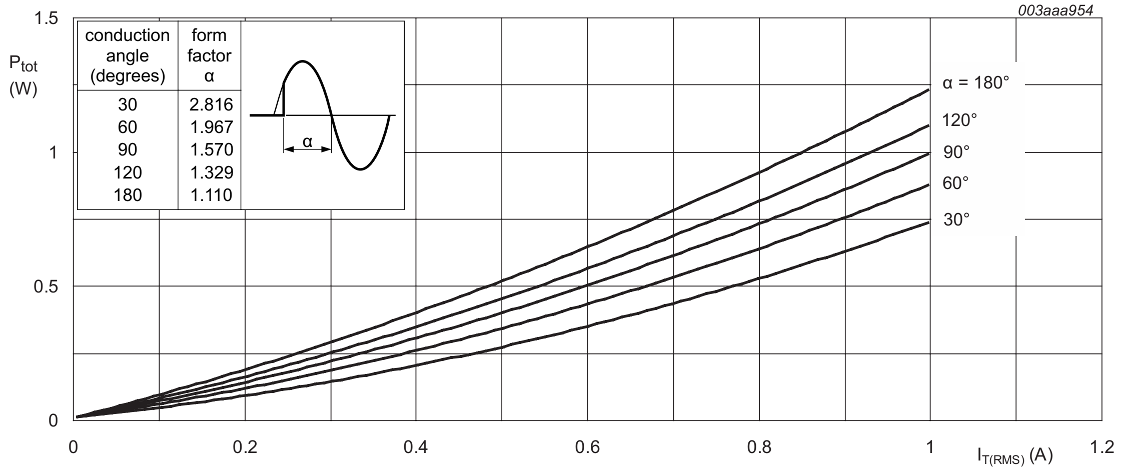


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 54 °C

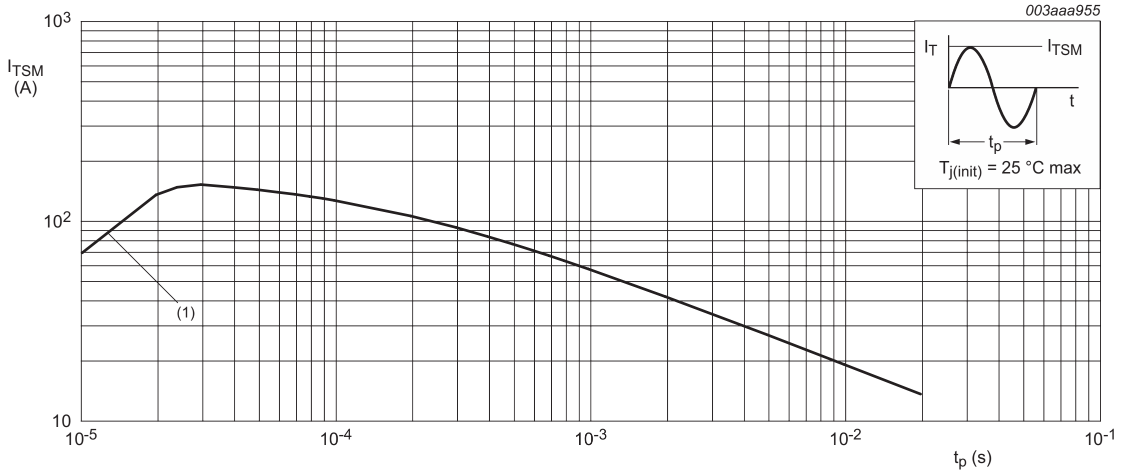
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

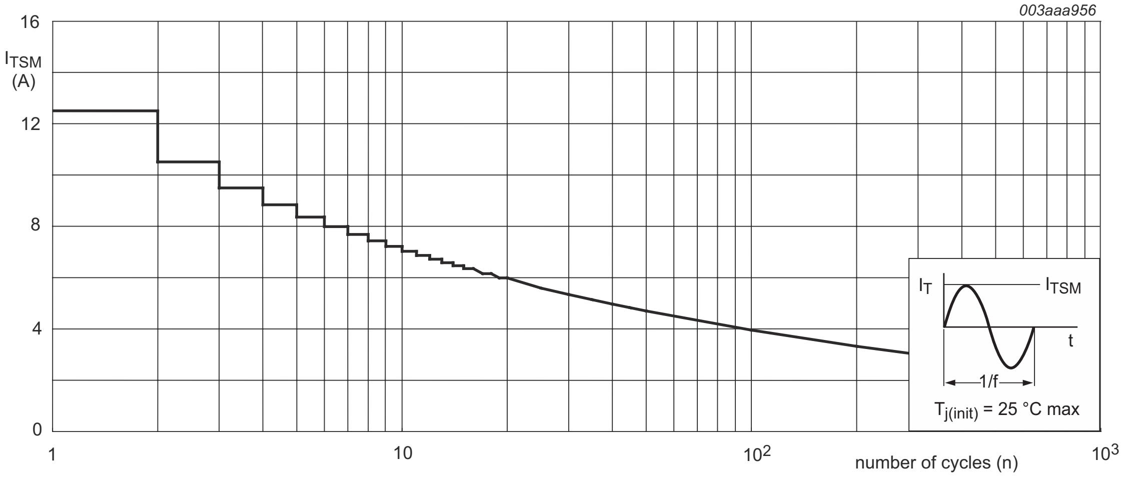
Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



$t_p \leq 20$ ms ;

(1) dI_T/dt limit

Fig. 4. Total power dissipation as a function of RMS on-state current; maximum values



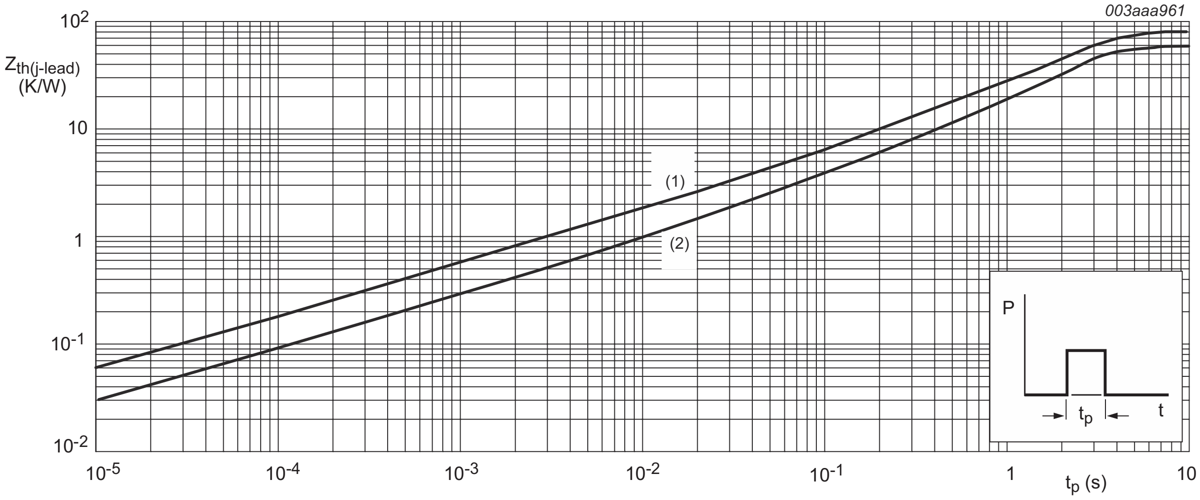
f = 50 Hz

Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6		-	-	60	K/W
		half cycle; Fig. 6		-	-	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	150	-	K/W



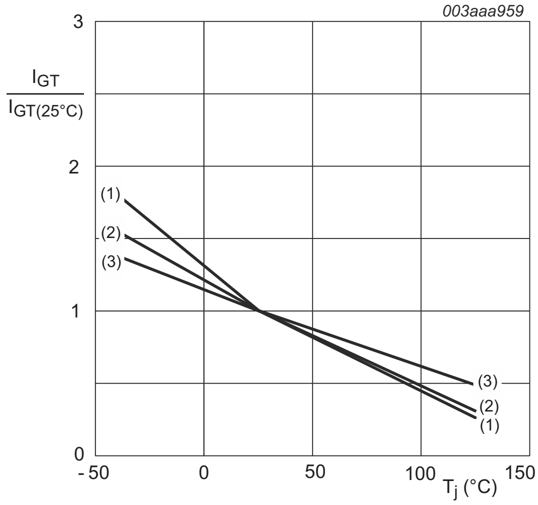
(1) Unidirectional (half cycle)
(2) Bidirectional (full cycle)

Fig. 6. Transient thermal impedance from junction to lead as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		1	-	10	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		1	-	10	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		1	-	10	mA
I_L	latching current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	12	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	20	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	12	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	12	mA
V_T	on-state voltage	I_T = 1.4 A; T_j = 25 °C; Fig. 10		-	1.2	1.5	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.7	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C		0.2	0.3	-	V
I_D	off-state current	V_D = 800 V; T_j = 125 °C		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12		600	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit		2.5	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 10 V/µs; gate open circuit		3.5	-	-	A/ms



(1) T2- G-
(2) T2+ G-
(3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

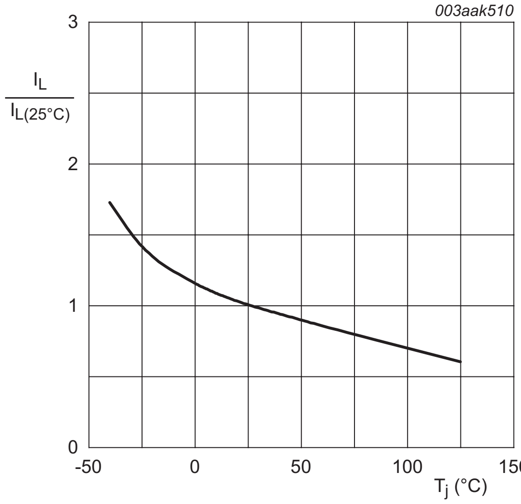


Fig. 8. Normalized latching current as a function of junction temperature

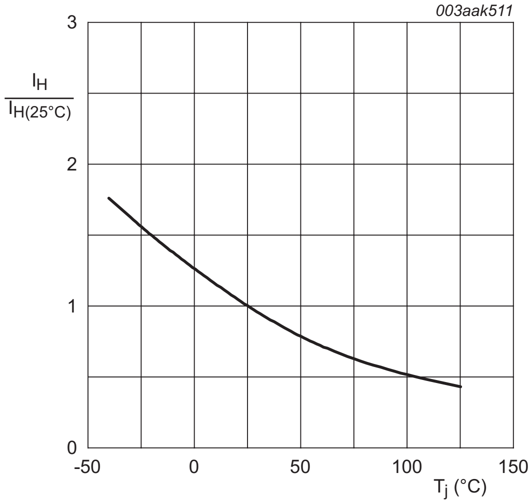
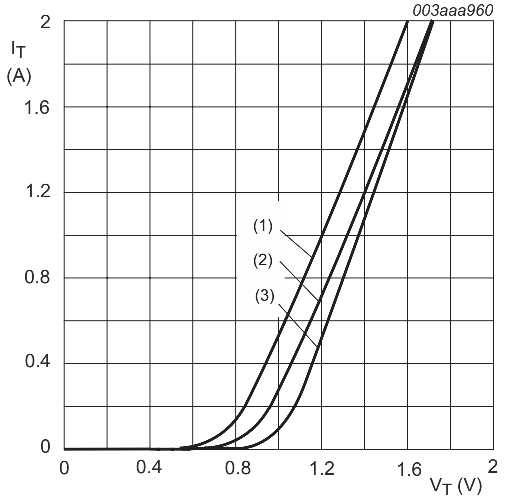


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.02 V; R_s = 0.358 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

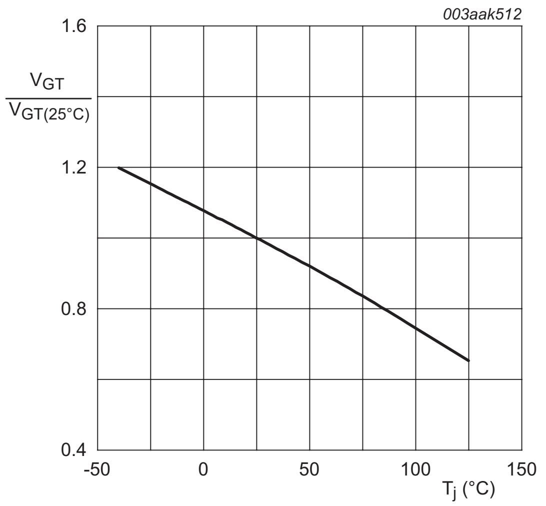


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

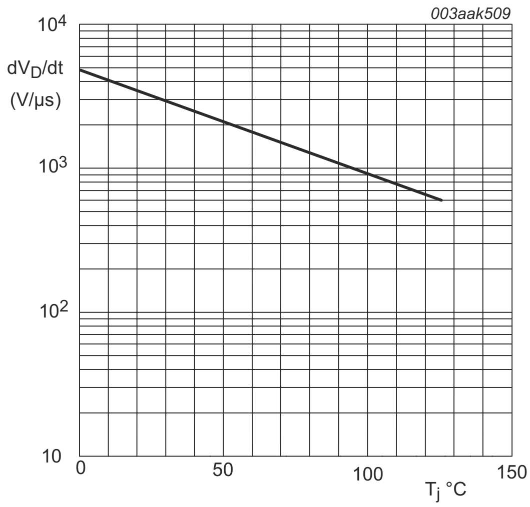
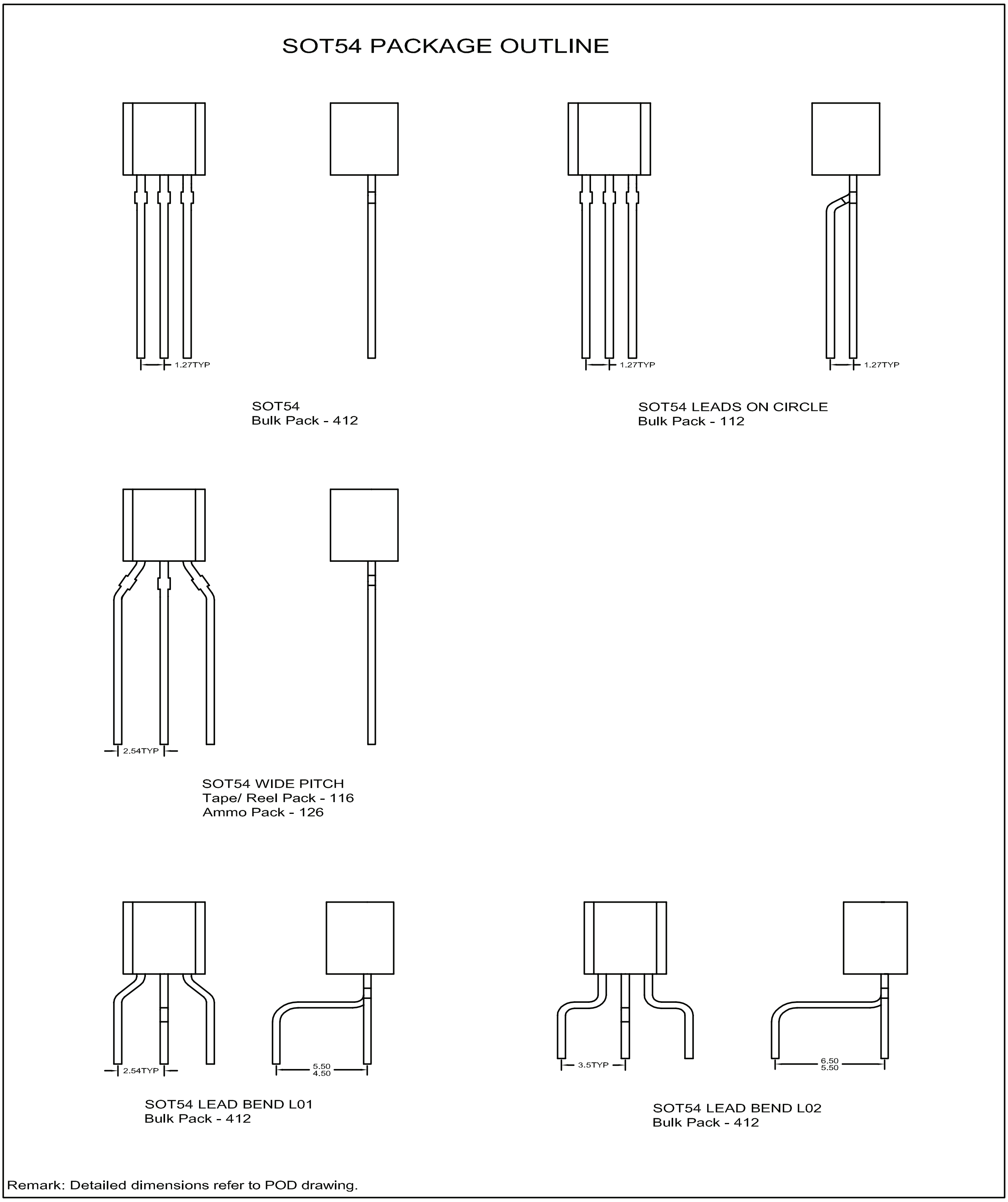


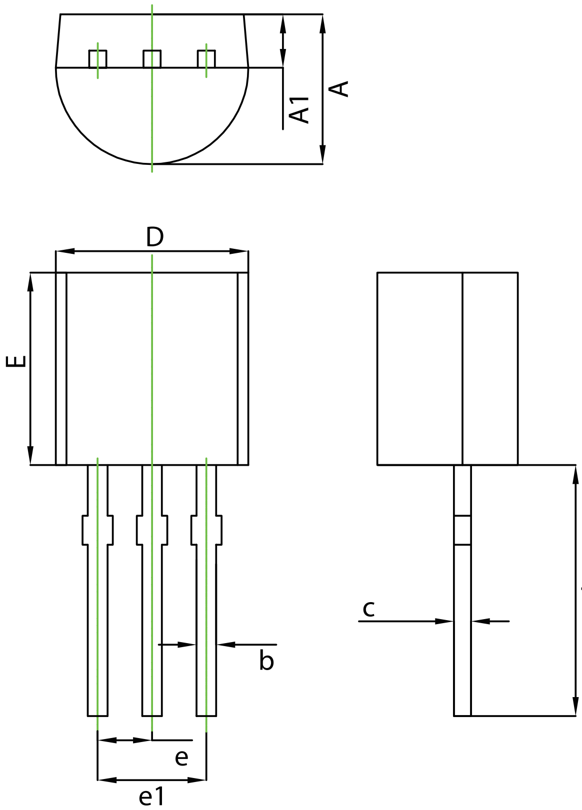
Fig. 11. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

11. Package outline



· PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.

Plastic single-ended leaded(through hole) package; 3 leads TO92



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
E	4.300	4.700	0.169	0.185
e	1.270 TYP.		0.050 TYP.	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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